# EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| S1 | 8 | (("5198683") or ("5670803") or ("5994735") or ("5627390")).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/07/05 14:06 |
| S2 | 2 | "20040140502" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 11:51 |
| S3 | 208 | suzuki-yasumichi.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:06 |
| S4 | 5 | suzuki-yasumichi.in. and 'SRAM' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:12 |
| S5 | 2 | suzuki-yasumichi.in. and 'MISFET' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:08 |
| S6 | 252 | @ad<="20040114" and 'vertical' with 'MISFET' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:11 |
| S7 | 864 | (257/328).ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:09 |
| S8 | 826 | @ad<="20040114" and (257/903).ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 13:22 |
| S9 | 238 | @ad<="20040114" and (257/322).ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:10 |
| S10 | 785 | @ad<="20040114" and (257/e21.661).ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:10 |

| S11 | 634 | @ad<="20040114" and (257/e27. 098).ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:10 |
|-----|------|------|------|------|------|------|
| S12 | 214 | @ad<="20040114" and (438/212). ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:43 |
| S13 | 630 | @ad<="20040114" and (438/268). ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:11 |
| S14 | 1036 | @ad<="20040114" and (438/197). ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:11 |
| S15 | 55 | @ad<="20040114" and (438/198). ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:11 |
| S16 | 194 | @ad<="20040114" and 'vertical' and 'MISFET' and 'SRAM' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 10:07 |
| S17 | 107 | IWAI-HIDETOSHI.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 15:34 |
| S18 | 18 | IWAI-HIDETOSHI.in. and 'SRAM' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 14:12 |
| S19 | 34 | IWAI-HIDETOSHI.in. and 'mask' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/07/05 15:34 |
| S20 | 156 | @ad<="20040114" and 'vertical' and 'MISFET' and 'SRAM' and 'mask' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 14:06 |
| S21 | 19 | 'Murata' and 'Renesas' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 09:09 |

| S22 | 144 | 'nakamura' and 'Renesas' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 09:11 |
|-----|-----|--------------------------|---------------------------------------------|----|----|------------------|
| S23 | 294 | 'suzuki' and 'Renesas' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 09:11 |
| S24 | 36 | 'suzuki' and 'Renesas' and 'vertical' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 09:11 |
| S25 | 43 | 'suzuki' and 'Renesas' and 'SRAM' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 09:11 |
| S26 | 22 | 'nakamura' and 'Renesas' and 'SRAM' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 09:11 |
| S27 | 88 | @ad<="20040114" and 'vertical MISFET' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:25 |
| S28 | 686 | @ad<="20040114" and 'SRAM' and 'MISFET' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:16 |
| S29 | 1 | "5936280".PN. | USPAT; USOCR | OR | ON | 2005/10/04 10:11 |
| S30 | 264 | @ad<="20040114" and 'SRAM' and 'MISFET' and 'dielectric' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:08 |
| S31 | 2 | ("6483136").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/04 10:39 |
| S32 | 1 | "5472893".PN. | USPAT; USOCR | OR | ON | 2005/10/04 10:41 |

| S34 | 7 | @ad<="20040114" and 'vertical' with 'FET' and 'first dielectric' and 'second dielectric' and 'third dielectric' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:10 |
|---|---|---|---|---|---|---|
| S35 | 171 | @ad<="20040114" and 'vertical' with 'conductive' and 'first dielectric' and 'second dielectric' and 'third dielectric' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:10 |
| S36 | 0 | @ad<="20040114" and 'MISFET' and 'conductive side wall' and 'first dielectric' and 'second dielectric' and 'third dielectric', | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 16:11 |
| S37 | 2 | @ad<="20040114" and 'MISFET' and 'conductive side wall' and 'dielectric' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:11 |
| S39 | 6 | @ad<="20040114" and 'MISFET' and 'conductive sidewall' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:17 |
| S40 | 111 | @ad<="20040114" and 'columnar' and 'conductive' with 'side wall' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:18 |
| S41 | 273 | @ad<="20040114" and 'columnar' and 'conductive' with ('side wall' or 'sidewall') | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:35 |
| S42 | 2237 | @ad<="20040114" and 'vertical' with 'FET' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:38 |
| S43 | 18 | @ad<="20040114" and 'columnar' and 'conductive' with ('side wall' or 'sidewall') and 'RAM' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:35 |
| S44 | 627 | @ad<="20040114" and 'vertical' with 'FET' and 'memory' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:38 |
| S45 | 99 | @ad<="20040114" and (438/222). ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:43 |

| S46 | 83 | @ad<="20040114" and (438/206). ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 11:43 |
|-----|-----|-----|-----|-----|-----|-----|
| S47 | 0 | 'masaru hisamoto' and 'hitachi' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 13:23 |
| S48 | 136 | 'hisamoto' and 'hitachi' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 13:23 |
| S49 | 114 | @ad<="20040114" and 'MISFET' and 'dielectric' same 'cvd' same 'temperature' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 14:07 |
| S51 | 0 | @ad<="20040114" and 'silicon nitride' same 'depostition' same 'cvd' same 'temperature' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 14:08 |
| S53 | 448 | @ad<="20040114" and 'silicon nitride' with 'deposition' same 'cvd' with 'temperature' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 14:09 |
| S54 | 246 | @ad<="20040114" and 'silicon nitride' with 'deposition' with 'cvd' with 'temperature' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 14:09 |
| S55 | 165 | 'TEOS' same 'CVD' with 'tetraethoxysilane' same 'silicon nitride' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 14:52 |
| S56 | 53 | 'TEOS' same 'CVD' with 'tetraethoxysilane' with 'silicon nitride' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 14:52 |
| S57 | 53 | 'TEOS' with 'CVD' with 'tetraethoxysilane' with 'silicon nitride' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:12 |
| S58 | 106 | 'silicon nitride' with 'silicon oxide' with 'Cvd' same 'tetraethoxysilane' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:00 |

| S59 | 441 | @ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:15 |
|---|---|---|---|---|---|---|
| S60 | 184 | @ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane' and 'ozone' and 'temperature' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:15 |
| S61 | 27 | @ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane' same 'ozone' same 'temperature' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:41 |
| S62 | 4 | @ad<="20040114" and 'TEOS' with 'silicon oxide' with 'CVD' with 'tetraethoxysilane' same 'ozone' same 'plasma' with 'density' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:47 |
| S65 | 24 | @ad<="20040114" and 'silicon oxide' with 'CVD' same 'plasma density' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:48 |
| S66 | 23 | @ad<="20040114" and 'silicon oxide' with 'CVD' same 'plasma density' and '10' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:49 |
| S67 | 3 | @ad<="20040114" and 'silicon oxide' with 'CVD' same 'plasma density' and '"10.sup.11"' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:51 |
| S68 | 4 | @ad<="20040114" and 'silicon oxide' same 'CVD' same 'plasma density' and '"10.sup.11"' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 15:51 |
| S70 | 422 | @ad<="20040114" and 'MISFET' and 'hitachi' and 'SRAM' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 16:16 |
| S73 | 2 | @ad<="20040114" and 'MISFET' and 'hitachi' and 'SRAM' and 'elliptical' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 16:16 |
| S74 | 7 | @ad<="20040114" and 'MISFET' and 'SRAM' and 'elliptical' | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/04 16:17 |